

## In the Specification

C1 [0015] The structure of FIG. 1 is subjected to an inventive etch as described above. An exemplary etch includes processing the wafer in a chamber of an AME5000 etch chamber. After placing the wafer substrate assembly in the etch chamber,  $O_2$  and  $CHF_3$  or  $CH_2F_2$  are introduced into the chamber at flow rates of about 60 sccm and about 20 sccm respectively. Pressure is maintained at between about 30 millitorr and about 40 millitorr, and a power of between about 300 watts and about 400 watts is utilized. At a chuck temperature of about  $10^\circ C$  and a sidewall temperature of about  $20^\circ C$ , the silicon nitride will etch at a rate of about  $720 \text{ \AA}/\text{min}$  in the vertical direction, and about  $180 \text{ \AA}/\text{min}$  in the horizontal direction. Generally, the vertical:horizontal etch rate will be about 4:1. For the  $525 \text{ \AA}$  thick layer of silicon nitride depicted in FIG. 1, the etch is performed ~~in the absence of a photoresist layer~~ for between about 35 seconds and about 60 seconds which results in the structure of FIG. 2. Spacers 32 having a width of about  $300 \text{ \AA}$  to about  $400 \text{ \AA}$  are formed.